N-Channel Field Effect Transistor

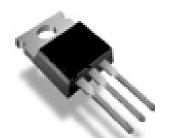
60N035

Advance Information

Description

The Bay Linear n-channel power field effect transistors are produced using high cell density DMOS technology , These devices are particularly suited for low voltage applications such as automotive and other battery powered circuits where fast switching, low in-line power loss and resistance to transistors are needed.

The TO-220 is offered in a 3-pin is universally preferred for all commercial-industrial applications at power dissipation level to approximately to 50 watts. Also, available in a D^2 surface mount power package with a power dissipation up to 2 Watts



Features

- Critical DC Electrical parameters specified at elevated Temp.
- Rugged internal source-drain diode can eliminate the need for external Zener diode transient suppresser
- Super high density cell design for extremely low R_{DS(ON)}

$$\begin{split} V_{DSS} &= 30V \\ R_{DS \; (ON)} &= 0.015 \; \Omega \\ I_D &= 60 A \end{split}$$

Ordering Information

| Device | Package | Temp. |
|---------|---------------------------|------------|
| 60N035T | TO-220 | 0 to 150°C |
| 60N035S | TO-263 (D ²) | 0 to 150°C |

Absolute Maximum Rating

| Symbol | Parameter | Max | Unit |
|--------------|--|------------|------|
| I_D | Drain Current | | |
| | Continues | 60 | A |
| | Pulsed | 180 | |
| $V_{ m DSS}$ | Drain-Source Voltage | 30 | V |
| V_{GSV} | Gate Source Voltage | ±20 | V |
| P_{D} | Total Power Dissipation @ T _C =25°C | 50 | W |
| | Derate above 25°C | 0.4 | W/°C |
| $T_{ m J}$ | Operating and Storage | -65 to 175 | °C |
| T_{STG} | Temperature Range | | -C |

Electrical Characteristics ($T_C = 25$ °C unless otherwise specified)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units | | | |
|-------------------------------------|------------------------------------|---|------|-------|----------------|-------|--|--|--|
| OFF CHARACTERSTICS | | | | | | | | | |
| $\mathbf{BV}_{\mathbf{DSS}}$ | Drain source breakdown voltage | V _{GS} =0V, I _D =250μA | 30 | | | V | | | |
| $\mathbf{I}_{	ext{DSS}}$ | Zero Gate Voltage Drain Current | V _{DS} =24V V _{GS} =0V | | | 10 | μΑ | | | |
| I_{GBLF} | Gate-Body Leakage Forward | $V_{GS}=20V$ $V_{DS}=0V$ | | | 100 | nA | | | |
| I_{GBLR} | Gate-Body Leakage Reverse | $V_{GS}=20V$ $V_{DS}=0V$ | | | -100 | nA | | | |
| ON CHAR | ACTERSTICS | | | | | | | | |
| V_{GS} | Gate Threshold Voltage | $V_{DS}=V_{GS}$ $I_{D}=250\mu A$ | 1 | | 3 | V | | | |
| R _{DS(ON)} | Static Drain Voltage | V _{GS} =10V, I _D =26A V _{CS} =4.5V, I _O =21A | | 0.014 | 0.015 0.025 | Ω | | | |
| $I_{D(ON)}$ | ON-State Drain Current | V _{GS} =10V | 60 | | | A | | | |
| $\mathbf{g}_{\mathbf{f}\mathbf{s}}$ | Forward Tran conductance | | | | | | | | |
| DYNAMIC | CHARACTRISTICS | | 49 | | | | | | |
| C_{ISS} | Input Capacitance | $V_{DS} = 15V, V_{GS} = 0V$ | 2 15 | | 1500 | рF | | | |
| Coss | Output Capacitance | F=1.0 MHZ | Ch | | 700 | рF | | | |
| C_{RSS} | Reverse Tras. Capacitance | 1'-1:0 WH12 | | | 300 | рF | | | |
| SWITCHIN | IG CHARACTERSTICS | 36.3 | | | | | | | |
| $\mathbf{t_{D(ON)}}$ | Turn-ON Delay Time | $V_{DD}=15V$ | | | 60 | | | | |
| $\mathbf{t_r}$ | Turn-ON Rise Time | I_D =52A, V_{DS} =10V R_{GEN} =25 Ω | | | 200 | nS | | | |
| $t_{d(off)}$ | Turn-OFF Delay Time | | | | 50 | | | | |
| $\mathbf{t_F}$ | Turn-OFF Fall Time | | | | 120 | | | | |
| SOURCE D | RAIN DIODE CHRACTERIS | | | | | | | | |
| I_S | Maxim Continuous Drain sour | ce Diode Forward Current | | | 60 | A | | | |
| V _{DS} (note) | Drain Source Diode Forward Votlage | V_{GS} =0V I_{S} =26A | | | 1.35 | V | | | |
| THERMAI | CHRACTERISTICS | · · · · · · · · · · · · · · · · · · · | l. | | | | | | |
| $\mathbf{R}_{\mathbf{JC}}$ | Thermal Resistance, Junction t | to Case | | | 2.5 | °C/W | | | |
| R_{JC} | Thermal Resistance, Junction t | to Ambient | | | 62.5 | °C/W | | | |

Note: Pulse Test: Pulse With $\leq 300 \mu S$, Duty Cycle $\leq 2.0\%$

Advance Information- These data sheets contain descriptions of products that are in development. The specifications are based on the engineering calculations, computer simulations and/ or initial prototype evaluation.

Preliminary Information- These data sheets contain minimum and maximum specifications that are based on the initial device characterizations. These limits are subject to change upon the completion of the full characterization over the specified temperature and supply voltage ranges.

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